145 Adams Avenue, Hauppauge, NY 11788, USA
Tel: 1.631.435.1110 Fax: 1.631.435.1824
www.centralsemi.com

mailto:processchange@centralsemi.com
http://www.centralsemi.com/processchange

PCN # 252
Notification Date:
March 8, 2024

Product / Process Change Notice

Devices affected:
The CBRDFSH2-100 Schottky bridge rectifier manufactured in the BR DFN case.

Extent of change:
Change in wafer fab, resulting in change in die size from 45 x 45 mils to 46 x 46 mils (see Table 1).

Reason for change:
As part of Central Semiconductor's supply chain risk mitigation initiative, and in an effort to ensure an undisrupted supply of product, a change in wafer fabrication site is being made for the products referenced above. Product specifications, quality and reliability are not impacted by this change.

Effect of change:
This change does not affect the fit, form or function of the devices.

Earliest effective date of change:
March 8, 2024

Qualification data:

Test	Condition	Failure rate
High Temperature Storage Life (HTSL)	150°C (-0/+10)°C, 1000 hours. **JESD22-A103**	0/77
Temperature Cycling (TC)	T= -65°C to +150°C 1000 cycles. Dwell time = 15 min. **JESD22-A104 & MIL-STD-750 TM1051**	0/77
High Temperature Reverse Bias (HTRB)	T=125°C, t=1000 hours, Bias per device data sheet **JESD22-A108**	0/77
Thermal Shock (TS)	100 cycles, dwell time = 5 min, -65°C to +150°C, max transfer time = 20 sec. **JESD22-A106**	0/77
Unbiased Highly Accelerated Temperature and Humidity Stress Test (UHAST)	T = 110°C, RH = 85%, t = 264 hrs **JESD22-A110**	0/77
Highly Accelerated Temperature and Humidity Stress Test (HAST)	T = 110°C, RH = 85%, and t = 264 hours. Bias conditions per device specification sheet. **JESD22-A110**	0/77

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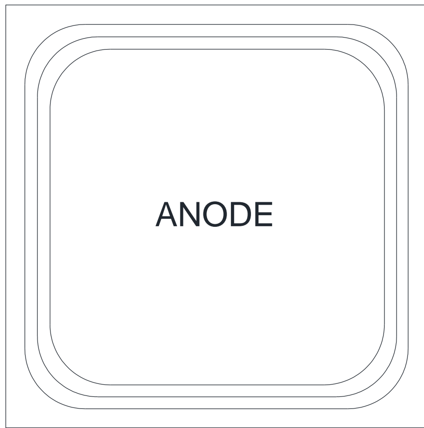
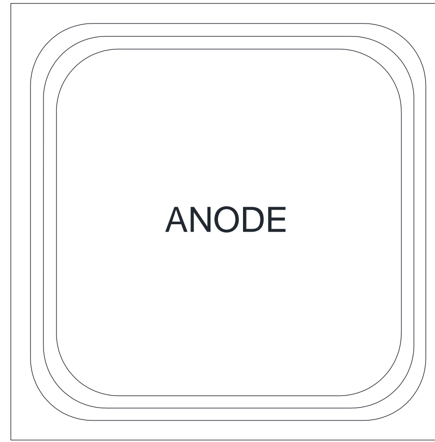
Table 1:

Before Change



After Change



Die Size	45 x 45 MILS
Die Thickness	10 MILS
Anode Bonding Pad Size	40 x 40 MILS
Top Side Metalization	Ti/Ni/Ag
Back Side Metalization	Ti/Ni/Ag

Die Size	46 x 46 MILS
Die Thickness	11.8 MILS
Anode Bonding Pad Size	41.8 X 41.8 MILS
Top Side Metalization	TiW/TiNi/Ag
Back Side Metalization	Ti/Ni/Ag

As per JEDEC standard JESD46, Customer Notification of Product/Process Changes by Solid-State Suppliers, a lack of acknowledgement of a PCN within thirty (30) days constitutes acceptance of the change.

The undersigned acknowledges and accepts Central Semiconductor's Product/Process Change Notification (PCN).

Company Name:	
Address:	
Printed Name:	
Title:	
Signature:	
Date:	